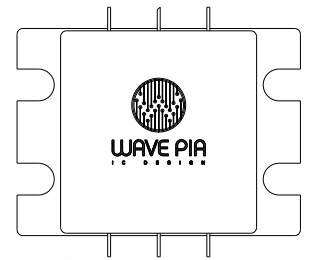


Product Features

- 50Ω Matched GaN HEMT for 5.03 to 5.09GHz
- 14.5dB Small Signal Gain at 5.06 GHz
- 25W Typical P_{SAT} at 5.06 GHz (CW)
- 26% Efficiency at P_{SAT} at 5.06 GHz (CW)
- 48V Operation

Applications

- Broadband Amplifiers
- Test Instrumentation
- Radar Application



Package Type: One-PKG

DC Characteristics¹ (TA=25°C)

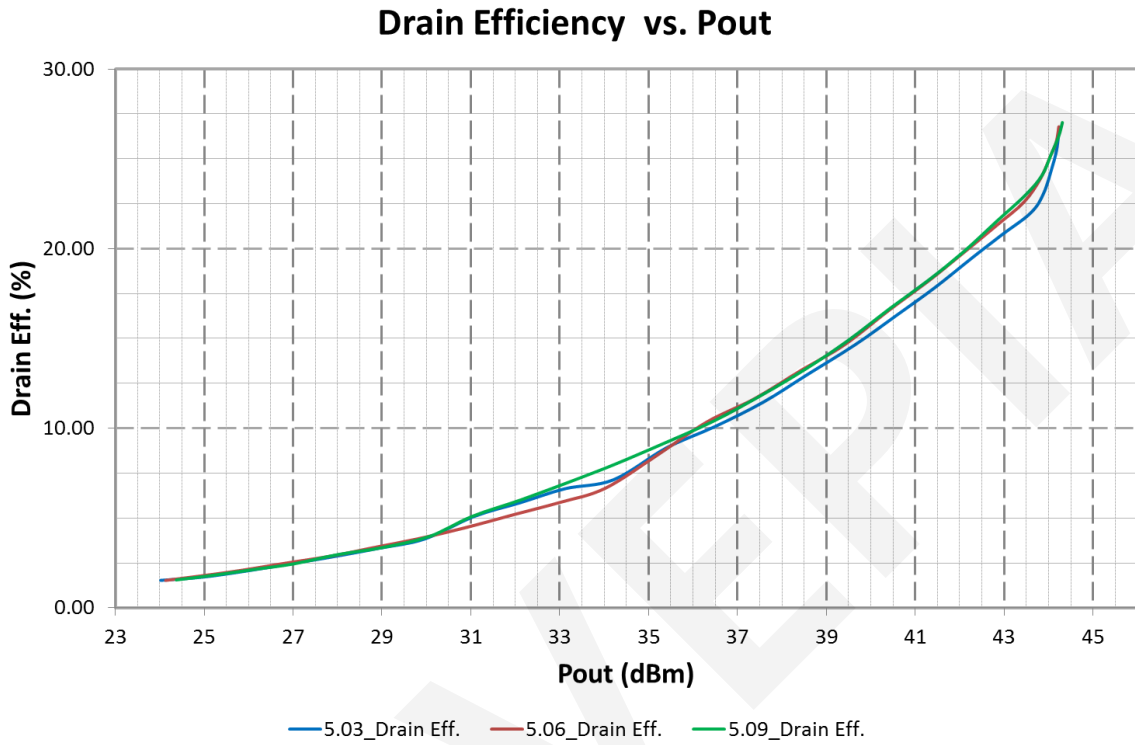
Parameter	Symbol	MIN	TYP	MAX	Units	Conditions
Gate Threshold Voltage	$V_{GS(th)}$		-3.1		V_{DC}	$V_{DS} = 48V$
Gate Quiescent Voltage	$V_{GS(Q)}$		-2.79		V_{DC}	$V_{DS} = 48V, I_D = 300mA$

RF Characteristics (TA = 25°C, F0 = 5.06GHz, VDD = 48V, IDQ = 200mA, unless otherwise noted)

Parameter	Symbol	MIN	TYP	MAX	Units	Conditions
Saturated Output Power	P_{SAT}		26		W	CW
Pulsed Drain Efficiency ¹	n		26		%	CW

1. Drain Efficiency = P_{OUT} / P_{DC}

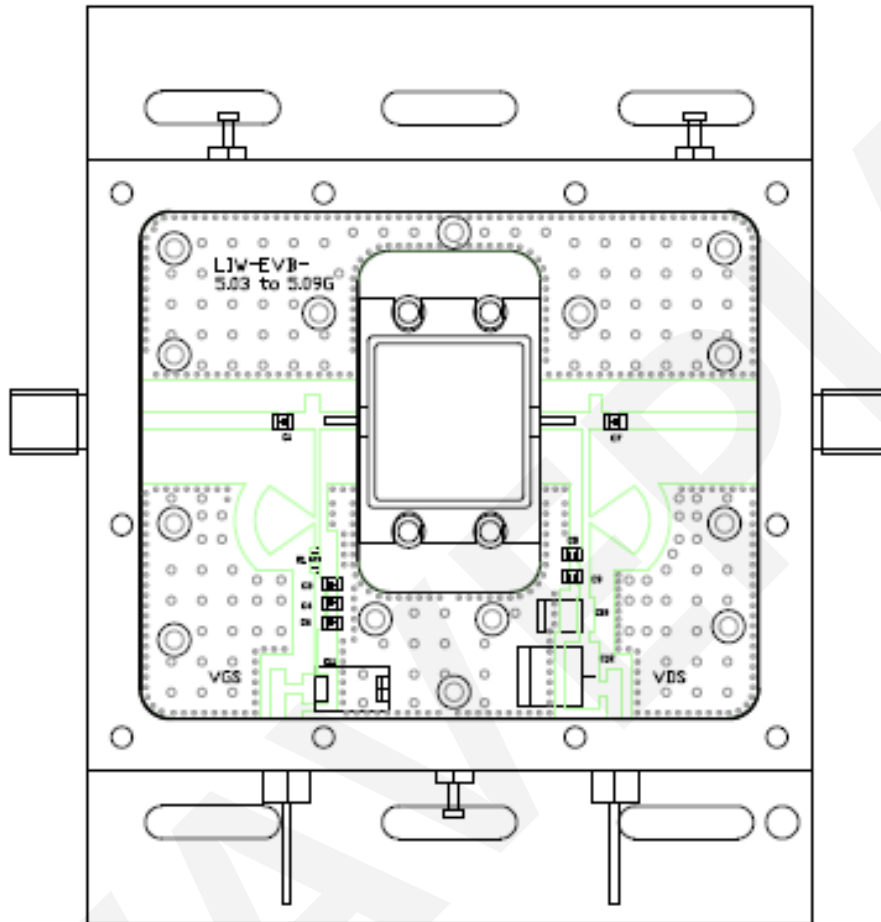
CW Signal Performance (TA=25°C, Measured in the test board amplifier circuit)
VDD = 48V, IDQ = 300mA



Small Signal Performance (TA=25°C, Measured in the test board amplifier circuit)
 VDD = 48V, IDQ = 300mA



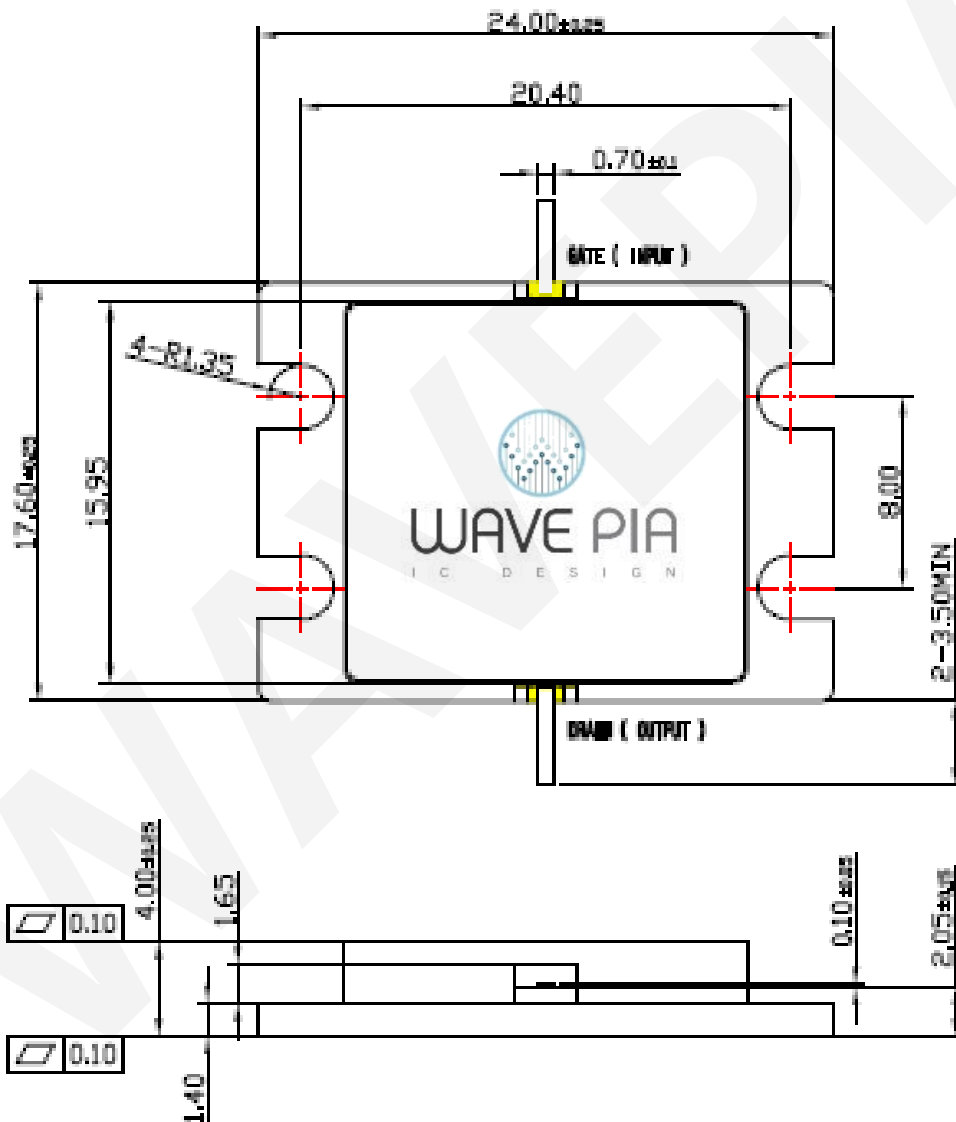
Evaluation Board



Reference Number	Value	Items	Package	Manufacturer
C1,C7	3.0pF	High Q Capacitor	CHA	TEMEX
C3,C8	5.6pF	High Q Capacitor	CHA	TEMEX
C4	100pF	Ceramic Capacitor	2010	Murata
C5	100nF	Ceramic Capacitor	2010	Murata
C11	22uF/16V	Tantalum Capacitor	-	-
C9	100pF	High Q Capacitor	CHA	TEMEX
C10	10pF	High Q Capacitor	CHA	TEMEX
C11	470nF	High V Capacitor	3528	Johanson Dielectrics
C12	47uF/100V	High V Tantalum Capacitor	-	-
R1	50Ω	Chip Resistor	2010	Walsin

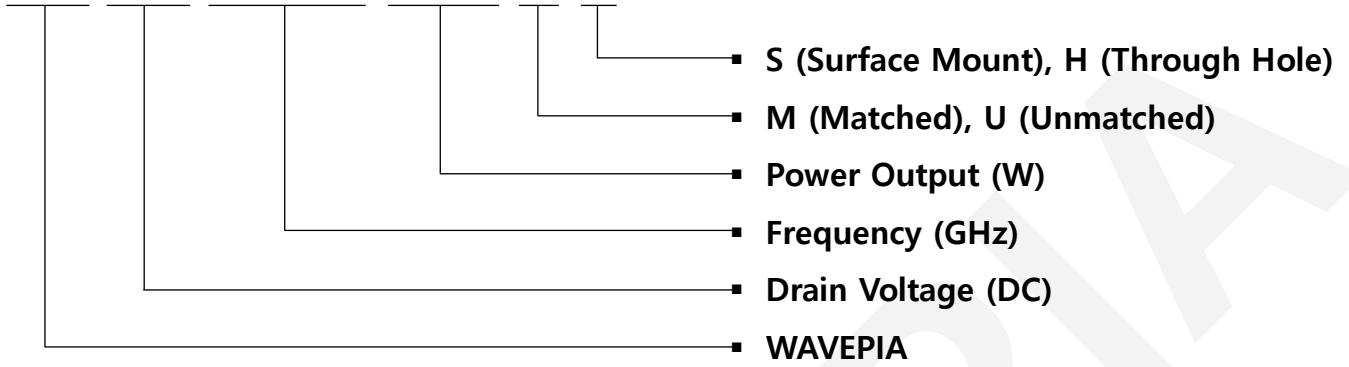
Product Dimension

- Package Type: One-PKG
- Unit: mm



Part Number System

W P 4 8 5 P 0 3 0 2 5 M H



Parameter	Value	Units
Drain Voltage	48	V
Lower Frequency	5.03	GHz
Upper Frequency	5.09	GHz
Output Power	25	W
Transistor Type	Matched	-
Package	Through Hole	-